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IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re application of:

Michael Geva, et al.

Serial No.: 09/757,099

Filed: January 8, 2001

For: ELECTRONIC DEVICE HAVING A BARRIER REGION
INCLUDING ALUMINUM AND A METHOD OF MANUFACTURE
THEREFOR

Group No.: 2874

Commissioner for Patents
Washington, D. C. 20231

Sir:

I hereby certify that this correspondence is being deposited with the United States Postal Service as first class mail in an envelope addressed to: Commissioner of Patents and Trademarks, Washington, D.C. 20231, on 7/17/2001 (Date)
Elizabeth Schumacher
(Printed or typed name of person signing the certificate)
Elizabeth Schumacher
(Signature of the person signing the certificate)
7-17-2001
(Date of Signature)

INFORMATION DISCLOSURE STATEMENT

In accordance with 37 C.F.R. §1.56 and the provisions of 37 C.F.R. §§1.97 and 1.98 and §609 of the Manual of Patent Examining Procedure, Applicant hereby makes a disclosure of the patents, publications and other information listed below and on the accompanying form PTO-1449, which may be potentially material to the patentability of the invention disclosed in the above-

referenced application. Pursuant to § 1.97(e) the Applicant hereby states that each item of information contained in the information disclosure statement was cited in a communication from a foreign patent office in a counterpart foreign application not more than three months prior to the filing of the information disclosure statement.

U.S. Patent No.

Inventor

Date

5,882,951
5,559,910
4,438,446

Bhat
Taga et al.
Tsang

March 16, 1999
September 24, 1996
March 20, 1984

Foreign Patent No.

Country

Date

97/50133
97/40560
0 715 380 A1
0 557 638 A2
0 518 320 A2

WO
WO
EP
EP
EP

31 December 1997
30 October 1997
5 June 1996
1 September 1993
16 December 1992

Ref:

K. Schimpf, J. Hollfelder, M. Horstmann, M. Marso, H. Hardtdegen and P. Kordos; "0.2um T-gate InP/InGaAs/InP pHEMT with InGaP diffusion barrier layer grown by LP-MOCVD using and N₂-carrier"; IPRM, SCHWABISCH-GMUND, 1996, pgs. 666-669 XP-002169035.

Applicant hereby certifies that each item of information contained in the Information Disclosure Statement was cited in a communication from a foreign patent office in a counterpart foreign application not more than three months prior to the filing of the statement.

As attorney for the Applicant, I am signing below on the basis of the information supplied by an individual designated in § 1.56(c).

Respectfully submitted,

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